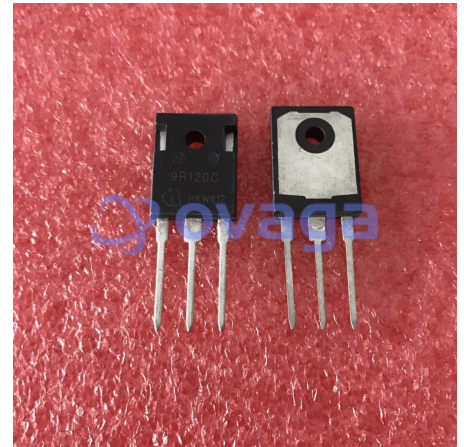


N-Channel MOSFETs (>500V...900V); Package: PG-TO247-3; VDS (max): 900.0 V;
 Package: TO-247; RDS(ON) @ TJ=25°C VGS=10: 120.0 mOhm; ID(max) @ TC=25°C:
 36.0 A; IDpuls (max): 96.0 A; MOSFET COOL MOS

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-247
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for IPW90R120C3 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

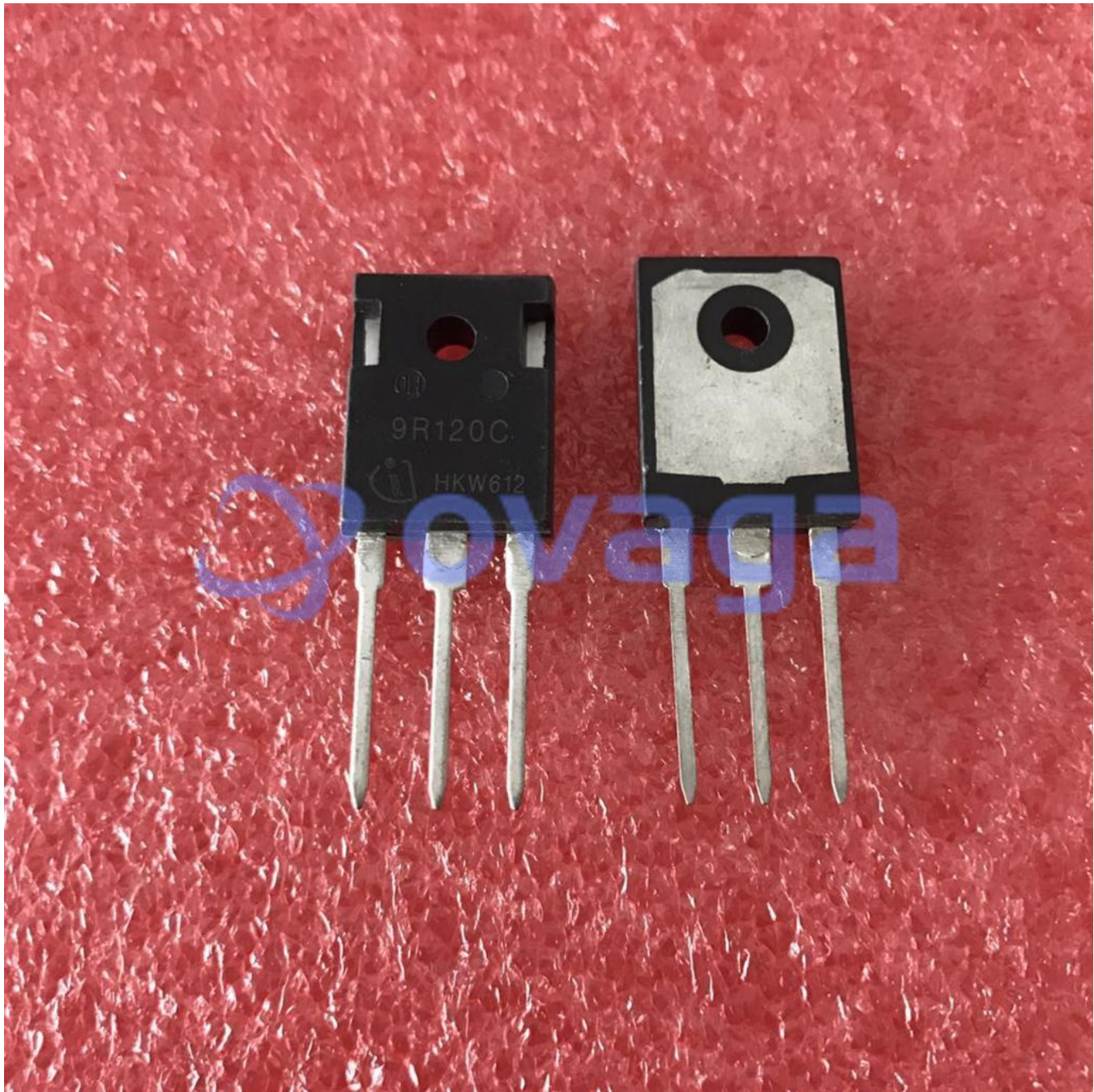
IPW90R120C3 is a power MOSFET transistor produced by Infineon Technologies. Here's some information about it:

Features

- 1200V breakdown voltage
- 0.09 Ohm maximum on-resistance (Rds(on)) at 25°C
- 90A maximum continuous drain current (Id)
- Fast switching speed
- Low gate charge
- RoHS compliant

Application

- Motor control
- Power supplies
- Solar inverters
- Welding equipment
- UPS



Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



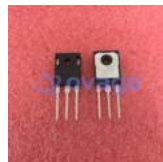
[IPB180N06S4-H1](#)

Infineon Technologies Corporation
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation
TDSON-8



[IPW65R080CFD](#)

Infineon Technologies Corporation
TO-247



[IPD25N06S4L-30](#)

Infineon Technologies Corporation
PG-TO252-3



[IPD180N10N3G](#)

Infineon Technologies Corporation
TO-252



[IPP60R074C6](#)

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TO-220-3



[IPD70R1K4P7S](#)

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TO252-3